

1 MHz Bandwidth Low Power Op Amp

Features

- Available in SC-70-5 and SOT-23-5 packages
- 1 MHz Gain Bandwidth Product (typ.)
- Rail-to-Rail Input/Output
- Supply Voltage: 1.8V to 5.5V
- Supply Current: $I_Q = 100 \mu A$ (typ.)
- 90° Phase Margin (typ.)
- Temperature Range:
 - Industrial: -40°C to +85°C
 - Extended: -40°C to +125°C
- Available in Single, Dual and Quad Packages

Applications

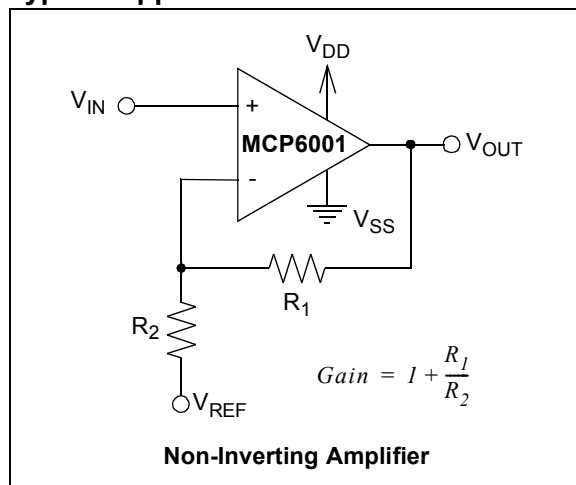
- Automotive
- Portable Equipment
- Photodiode Pre-amps
- Analog Filters
- Notebooks and PDAs
- Battery-Powered Systems

Available Tools

Spice Macro Models (at www.microchip.com)

FilterLab® Software (at www.microchip.com)

Typical Application

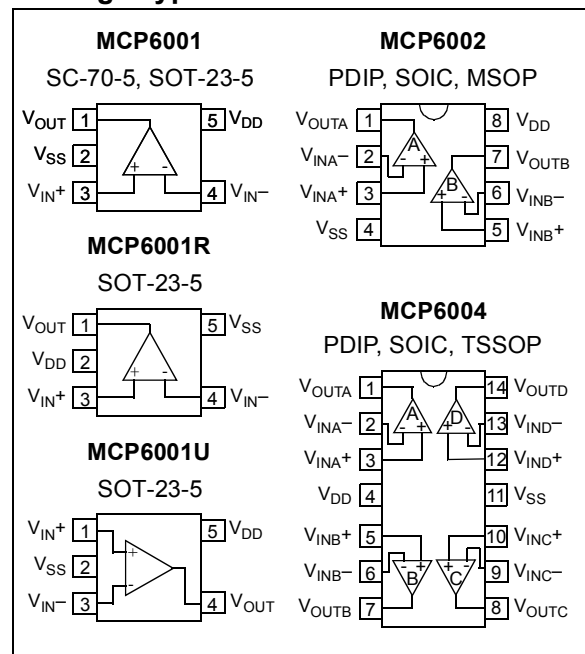


Description

The Microchip Technology Inc. MCP6001/2/4 family of operational amplifiers (op amps) is specifically designed for general-purpose applications. This family has a 1 MHz gain bandwidth product and 90° phase margin (typ.). It also maintains 45° phase margin (typ.) with 500 pF capacitive load. This family operates from a single supply voltage as low as 1.8V, while drawing 100 μA (typ.) quiescent current. Additionally, the MCP6001/2/4 supports rail-to-rail input and output swing, with a common mode input voltage range of $V_{DD} + 300 \text{ mV}$ to $V_{SS} - 300 \text{ mV}$. This family of operational amplifiers is designed with Microchip's advanced CMOS process.

The MCP6001/2/4 family is available in the industrial and extended temperature ranges. It also has a power supply range of 1.8V to 5.5V.

Package Types



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

$V_{DD} - V_{SS}$	7.0V
All Inputs and Outputs	$V_{SS} - 0.3V$ to $V_{DD} + 0.3V$
Difference Input Voltage	$ V_{DD} - V_{SS} $
Output Short Circuit Current	continuous
Current at Input Pins	± 2 mA
Current at Output and Supply Pins	± 30 mA
Storage Temperature	-65°C to $+150^{\circ}\text{C}$
Maximum Junction Temperature (T_J)	$+150^{\circ}\text{C}$
ESD Protection On All Pins (HBM;MM)	≥ 4 kV; 200V

† **Notice:** Stresses above those listed under “Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

PIN FUNCTION TABLE

Name	Function
V_{IN}^{+} , V_{INA}^{+} , V_{INB}^{+} , V_{INC}^{+} , V_{IND}^{+}	Non-inverting Inputs
V_{IN}^{-} , V_{INA}^{-} , V_{INB}^{-} , V_{INC}^{-} , V_{IND}^{-}	Inverting Inputs
V_{DD}	Positive Power Supply
V_{SS}	Negative Power Supply
V_{OUT} , V_{OUTA} , V_{OUTB} , V_{OUTC} , V_{OUTD}	Outputs

DC ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, $T_A = +25^{\circ}\text{C}$, $V_{DD} = +1.8V$ to $+5.5V$, $V_{SS} = \text{GND}$, $V_{CM} = V_{DD}/2$, $R_L = 10$ k Ω to $V_{DD}/2$, and $V_{OUT} \sim V_{DD}/2$.

Parameters	Sym	Min	Typ	Max	Units	Conditions
Input Offset						
Input Offset Voltage	V_{OS}	-7.0	—	+7.0	mV	$V_{CM} = V_{SS}$
Input Offset Drift with Temperature	$\Delta V_{OS}/\Delta T_A$	—	± 2.0	—	$\mu\text{V}/^{\circ}\text{C}$	$T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, $V_{CM} = V_{SS}$
Power Supply Rejection	PSRR	—	86	—	dB	$V_{CM} = V_{SS}$
Input Bias Current and Impedance						
Input Bias Current:	I_B	—	± 1.0	—	pA	$T_A = +85^{\circ}\text{C}$ $T_A = +125^{\circ}\text{C}$
Industrial Temperature	I_B	—	19	—	pA	
Extended Temperature	I_B	—	1100	—	pA	
Input Offset Current	I_{OS}	—	± 1.0	—	pA	
Common Mode Input Impedance	Z_{CM}	—	$10^{13} 6$	—	ΩpF	
Differential Input Impedance	Z_{DIFF}	—	$10^{13} 3$	—	ΩpF	
Common Mode						
Common Mode Input Range	V_{CMR}	$V_{SS} - 0.3$	—	$V_{DD} + 0.3$	V	
Common Mode Rejection Ratio	CMRR	60	76	—	dB	$V_{CM} = -0.3V$ to $5.3V$, $V_{DD} = 5V$
Open-Loop Gain						
DC Open-Loop Gain (large signal)	A_{OL}	88	112	—	dB	$V_{OUT} = 0.3V$ to $V_{DD} - 0.3V$, $V_{CM} = V_{SS}$
Output						
Maximum Output Voltage Swing	V_{OL} , V_{OH}	$V_{SS} + 25$	—	$V_{DD} - 25$	mV	$V_{DD} = 5.5V$
Output Short-Circuit Current	I_{SC}	—	± 6	—	mA	$V_{DD} = 1.8V$
		—	± 23	—	mA	$V_{DD} = 5.5V$
Power Supply						
Supply Voltage	V_{DD}	1.8	—	5.5	V	
Quiescent Current per Amplifier	I_Q	50	100	170	μA	$I_O = 0$, $V_{DD} = 5.5V$, $V_{CM} = 5V$

AC ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, $T_A = +25^{\circ}\text{C}$, $V_{DD} = +1.8$ to 5.5V , $V_{SS} = \text{GND}$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $R_L = 10\text{ k}\Omega$ to $V_{DD}/2$, and $C_L = 60\text{ pF}$.

Parameters	Sym	Min	Typ	Max	Units	Conditions
AC Response						
Gain Bandwidth Product	GBWP	—	1.0	—	MHz	
Phase Margin	PM	—	90	—	°	G = +1
Slew Rate	SR	—	0.6	—	V/ μs	
Noise						
Input Noise Voltage	E_{ni}	—	6.1	—	$\mu\text{Vp-p}$	f = 0.1 Hz to 10 Hz
Input Noise Voltage Density	e_{ni}	—	28	—	nV/ $\sqrt{\text{Hz}}$	f = 1 kHz
Input Noise Current Density	i_{ni}	—	0.6	—	fA/ $\sqrt{\text{Hz}}$	f = 1 kHz

TEMPERATURE SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, $V_{DD} = +1.8\text{V}$ to $+5.5\text{V}$, and $V_{SS} = \text{GND}$.

Parameters	Sym	Min	Typ	Max	Units	Conditions
Temperature Ranges						
Industrial Temperature Range	T_A	-40	—	+85	°C	
Extended Temperature Range	T_A	-40	—	+125	°C	
Operating Temperature Range	T_A	-40	—	+125	°C	(Note)
Storage Temperature Range	T_A	-65	—	+150	°C	
Thermal Package Resistances						
Thermal Resistance, 5L-SC70	θ_{JA}	—	331	—	°C/W	
Thermal Resistance, 5L-SOT-23	θ_{JA}	—	256	—	°C/W	
Thermal Resistance, 8L-PDIP	θ_{JA}	—	85	—	°C/W	
Thermal Resistance, 8L-SOIC (150 mil)	θ_{JA}	—	163	—	°C/W	
Thermal Resistance, 8L-SOIC (208 mil)	θ_{JA}	—	118	—	°C/W	
Thermal Resistance, 8L-MSOP	θ_{JA}	—	206	—	°C/W	
Thermal Resistance, 14L-PDIP	θ_{JA}	—	70	—	°C/W	
Thermal Resistance, 14L-SOIC	θ_{JA}	—	120	—	°C/W	
Thermal Resistance, 14L-TSSOP	θ_{JA}	—	100	—	°C/W	

Note: The industrial temperature devices operate over this extended temperature range, but with reduced performance. In any case, the internal Junction Temperature (T_J) must not exceed the Absolute Maximum specification of $+150^{\circ}\text{C}$.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25^\circ\text{C}$, $V_{DD} = +1.8\text{V}$ to $+5.5\text{V}$, $V_{SS} = \text{GND}$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $R_L = 10\text{ k}\Omega$ to $V_{DD}/2$, and $C_L = 60\text{ pF}$.

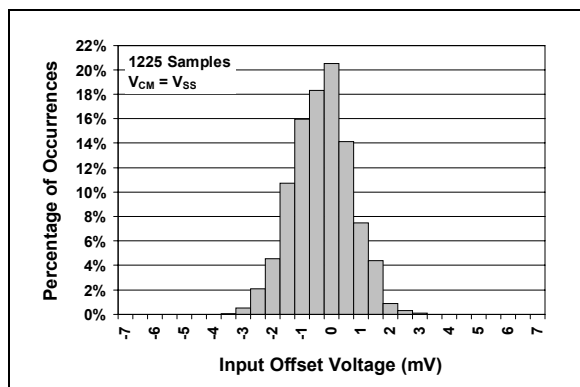


FIGURE 2-1: Input Offset Voltage Histogram.

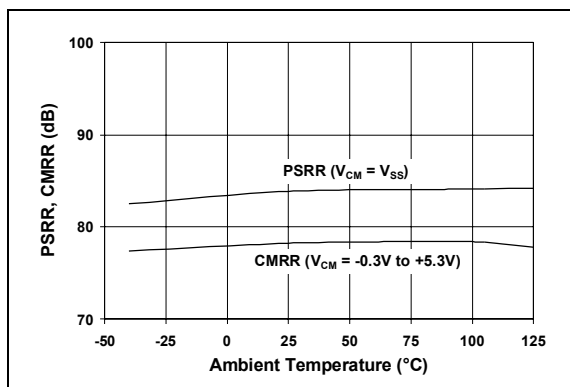


FIGURE 2-4: CMRR, PSRR vs. Ambient Temperature.

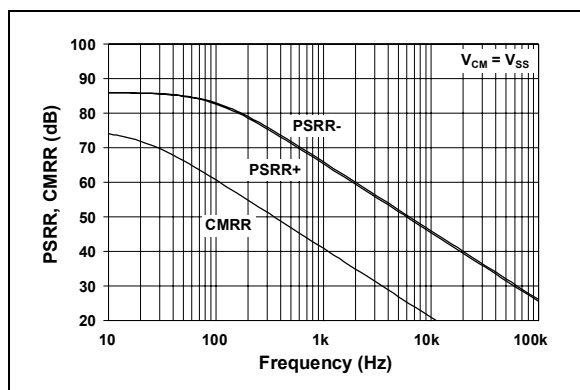


FIGURE 2-2: PSRR, CMRR vs. Frequency.

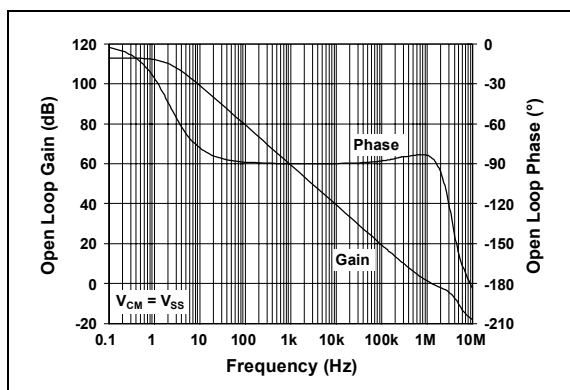


FIGURE 2-5: Open-Loop Gain, Phase vs. Frequency.

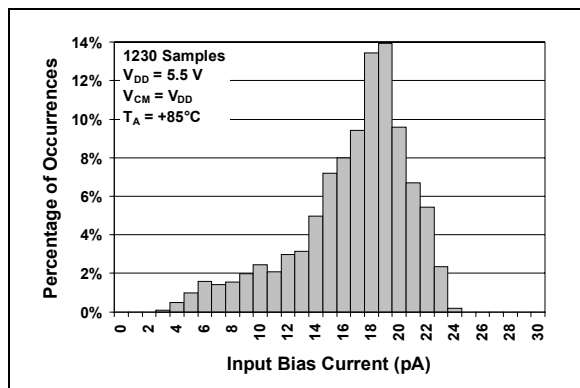


FIGURE 2-3: Input Bias Current at $+85^\circ\text{C}$ Histogram.

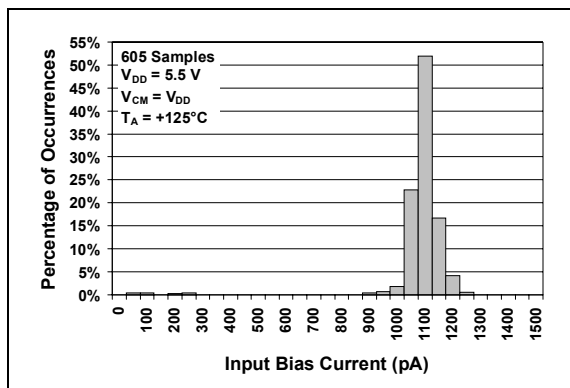


FIGURE 2-6: Input Bias Current at $+125^\circ\text{C}$ Histogram.

Note: Unless otherwise indicated, $T_A = +25^\circ\text{C}$, $V_{DD} = +1.8\text{V}$ to $+5.5\text{V}$, $V_{SS} = \text{GND}$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $R_L = 10\text{ k}\Omega$ to $V_{DD}/2$, and $C_L = 60\text{ pF}$.

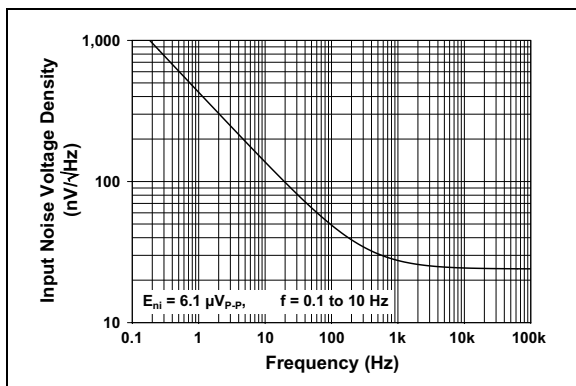


FIGURE 2-7: Input Noise Voltage Density vs. Frequency.

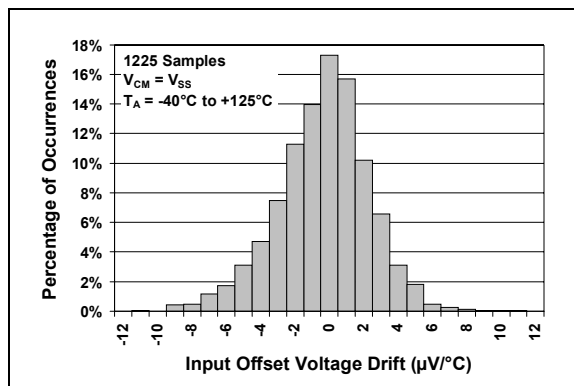


FIGURE 2-10: Input Offset Voltage Drift Histogram.

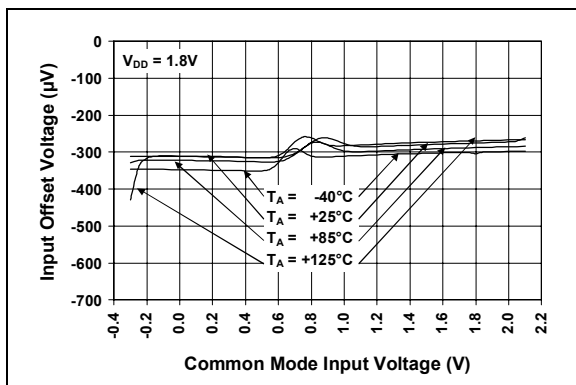


FIGURE 2-8: Input Offset Voltage vs. Common Mode Input Voltage at $V_{DD} = 1.8\text{V}$.

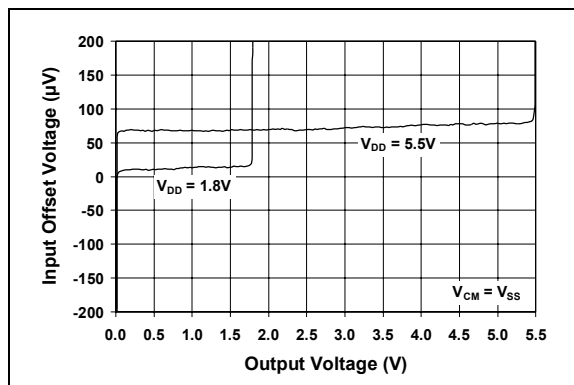


FIGURE 2-11: Input Offset Voltage vs. Output Voltage.

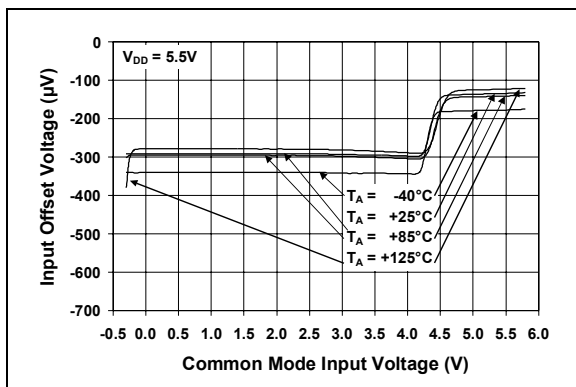


FIGURE 2-9: Input Offset Voltage vs. Common Mode Input Voltage at $V_{DD} = 5.5\text{V}$.

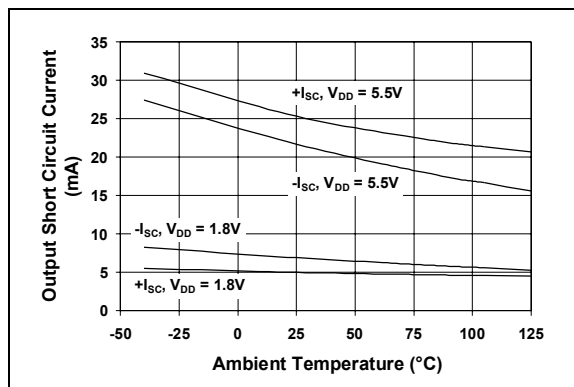


FIGURE 2-12: Output Short-Circuit Current vs. Ambient Temperature.

Note: Unless otherwise indicated, $T_A = +25^\circ\text{C}$, $V_{DD} = +1.8\text{V}$ to $+5.5\text{V}$, $V_{SS} = \text{GND}$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $R_L = 10\text{ k}\Omega$ to $V_{DD}/2$, and $C_L = 60\text{ pF}$.

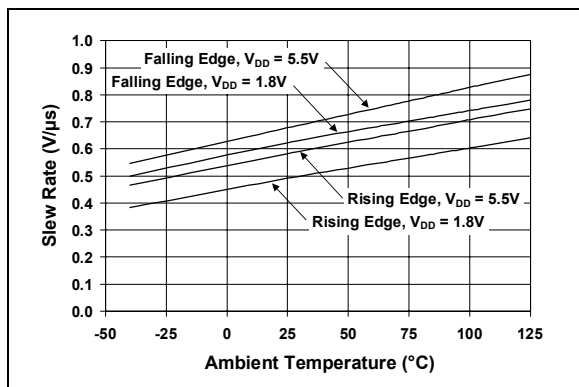


FIGURE 2-13: Slew Rate vs. Ambient Temperature.

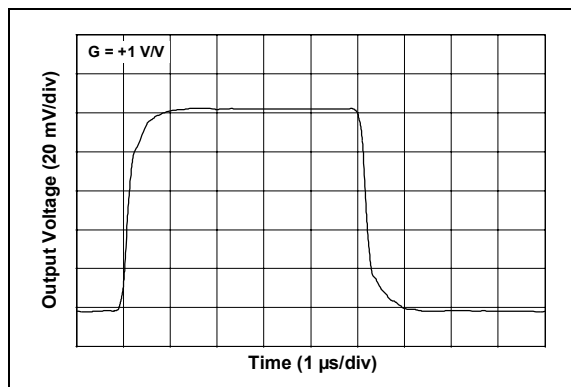


FIGURE 2-16: Small Signal Non-Inverting Pulse Response.

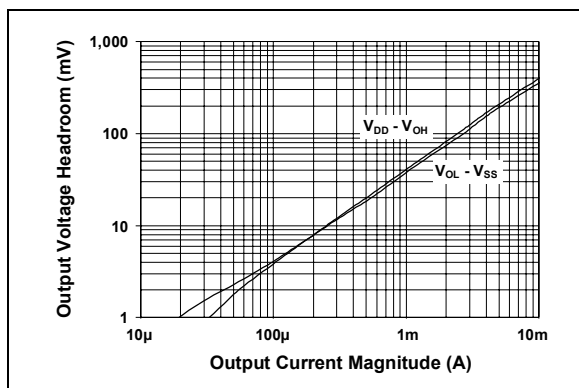


FIGURE 2-14: Output Voltage Headroom vs. Output Current Magnitude.

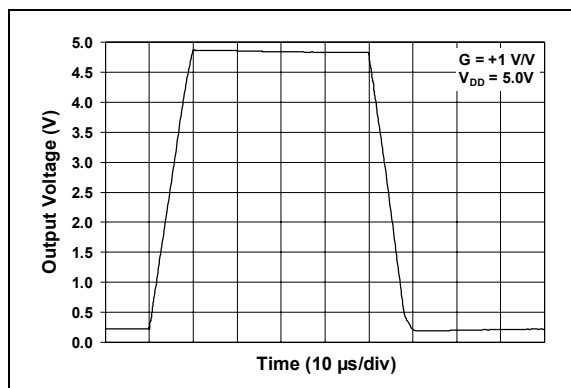


FIGURE 2-17: Large Signal Non-Inverting Pulse Response.

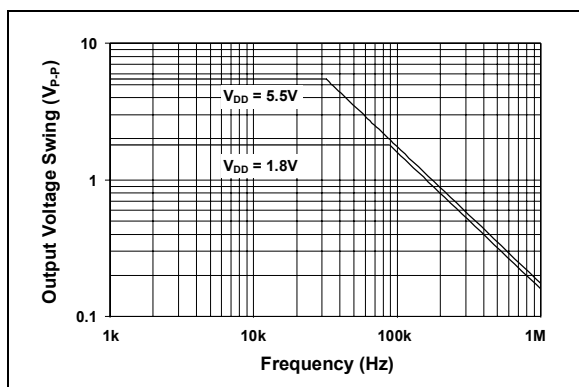


FIGURE 2-15: Output Voltage Swing vs. Frequency.

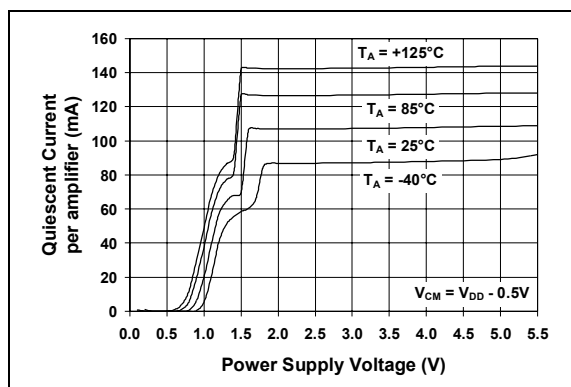


FIGURE 2-18: Quiescent Current vs. Power Supply Voltage.

3.0 APPLICATION INFORMATION

The MCP6001/2/4 family of op amps is manufactured using Microchip's state-of-the-art CMOS process and is specifically designed for low cost, low power and general-purpose applications. The low supply voltage, low quiescent current and wide bandwidth makes the MCP6001/2/4 ideal for battery-powered applications. This device has high phase margin, which makes it stable for larger capacitive load applications.

3.1 Rail-to-Rail Input

The MCP6001/2/4 op amp is designed to prevent phase reversal when the input pins exceed the supply voltages. Figure 3-1 shows the input voltage exceeding the supply voltage without any phase reversal.

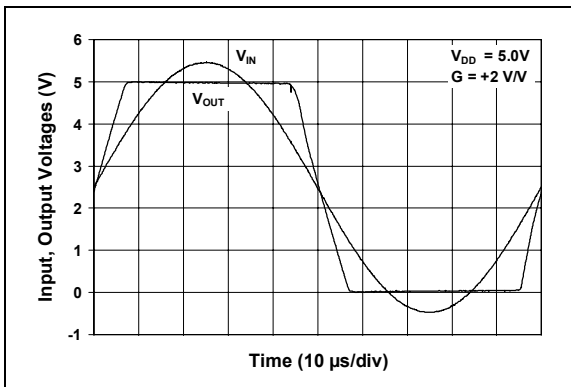


FIGURE 3-1: The MCP6001/2/4 Shows No Phase Reversal.

The input stage of the MCP6001/2/4 op amp uses two differential input stages in parallel; one operates at low common mode input voltage (V_{CM}) and the other at high V_{CM} . With this topology, the device operates with V_{CM} up to 300 mV above V_{DD} and 300 mV below V_{SS} . The Input Offset Voltage is measured at $V_{CM} = V_{SS} - 300$ mV and $V_{DD} + 300$ mV to ensure proper operation.

Input voltages that exceed the input voltage range ($V_{SS} - 0.3$ V to $V_{DD} + 0.3$ V at 25°C) can cause excessive current to flow into or out of the input pins. Current beyond ± 2 mA can cause reliability problems. Applications that exceed this rating must be externally limited with a resistor, as shown in Figure 3-2.

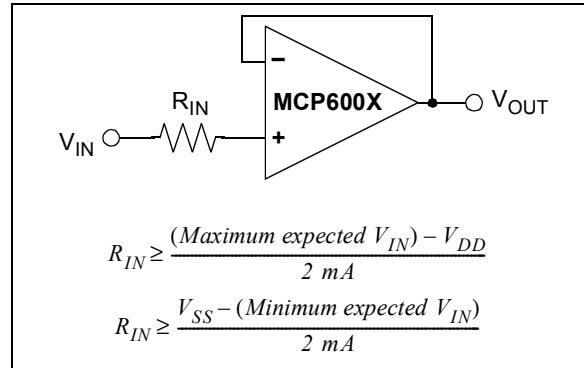


FIGURE 3-2: Input Current Limiting Resistor (R_{IN}).

3.2 Rail-to-Rail Output

The output voltage range of the MCP6001/2/4 op amp is $V_{DD} - 25$ mV (min.) and $V_{SS} + 25$ mV (max.) when $R_L = 10$ k Ω is connected to $V_{DD}/2$ and $V_{DD} = 5.5$ V. Refer to Figure 2-14 for more information.

3.3 Capacitive Loads

Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases, and the closed loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. A unity gain buffer ($G = +1$) is the most sensitive to capacitive loads, but all gains show the same general behavior.

When driving large capacitive loads with these op amps (e.g., > 100 pF when $G = +1$), a small series resistor at the output (R_{ISO} in Figure 3-3) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. It does not, however, improve the bandwidth.

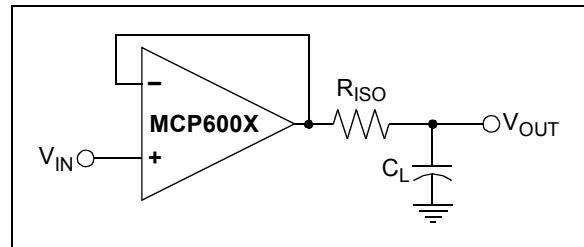


FIGURE 3-3: Output resistor, R_{ISO} stabilizes large capacitive loads.

To select R_{ISO} , check the frequency response peaking (or step response overshoot) on the bench (or with the MCP6001/2/4 Spice macro model). If the response is reasonable, you do not need R_{ISO} . Otherwise, start R_{ISO} at 1 k Ω and modify its value until the response is reasonable.

3.4 Supply Bypass

With this family of operation amplifiers, the power supply pin (V_{DD} for single supply) should have a local bypass capacitor (i.e., 0.01 μF to 0.1 μF) within 2 mm for good high frequency performance. It also needs a bulk capacitor (i.e., 1 μF or larger) within 100 mm to provide large, slow currents. This bulk capacitor can be shared with other parts.

3.5 PCB Surface Leakage

In applications where low input bias current is critical, PCB (printed circuit board) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is $10^{12}\Omega$. A 5V difference would cause 5 pA, if current-to-flow; this is greater than the MCP6001/2/4 family's bias current at 25°C (1 pA, typ).

The easiest way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 3-4.

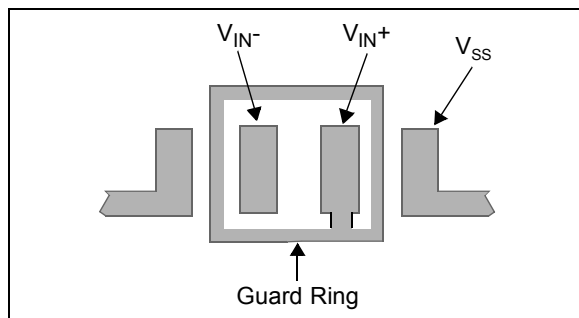


FIGURE 3-4: Example Guard Ring Layout for Inverting Gain.

1. Non-inverting Gain and Unity Gain Buffer:
 - a. Connect the non-inverting pin (V_{IN+}) to the input with a wire that does not touch the pcb surface.
 - b. Connect the guard ring to the inverting input pin (V_{IN-}). This biases the guard ring to the common mode input voltage.
2. Inverting and Transimpedance Gain Amplifiers (convert current to voltage, such as photo detectors):
 - a. Connect the guard ring to the non-inverting input pin (V_{IN+}). This biases the guard ring to the same reference voltage as the op amp (e.g., $V_{DD}/2$ or ground).
 - b. Connect the inverting pin (V_{IN-}) to the input with a wire that does not touch the PCB surface.

3.6 Application Circuits

3.6.1 UNITY GAIN BUFFER

The rail-to-rail input and output capability of the MCP6001/2/4 op amp is ideal for unity-gain buffer applications. The low quiescent current and wide bandwidth makes the device suitable for a buffer configuration in an instrumentation amplifier circuit, as shown in Figure 3-5.

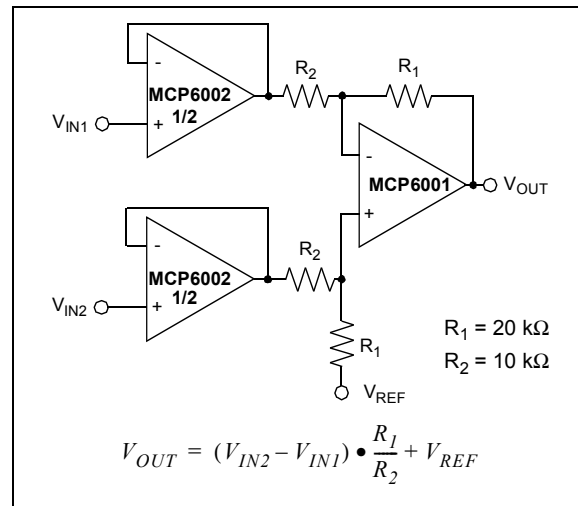


FIGURE 3-5: Instrumentation Amplifier with Unity Gain Buffer Inputs.

3.6.2 ACTIVE LOW-PASS FILTER

The MCP6001/2/4 op amp's low input bias current makes it possible for the designer to use larger resistors and smaller capacitors for active low-pass filter applications. However, as the resistance increases, the noise generated also increases. Parasitic capacitances and the large value resistors could also modify the frequency response. These trade-offs need to be considered when selecting circuit elements.

It is possible to have a filter cutoff frequency as high as 1/10th of the op amp bandwidth (100 kHz). Figure 3-6 shows a second-order butterworth filter with 100 kHz cutoff frequency and a gain of +1V/V.

The component values were selected using Microchip's FilterLab® software.

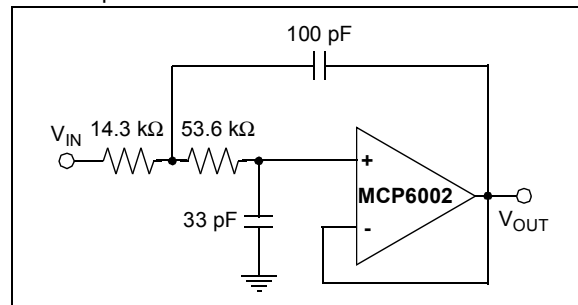


FIGURE 3-6: Active Second-Order Low-Pass Filter.

3.6.3 PEAK DETECTOR

The MCP6001/2/4 op amp has a high input impedance, rail-to-rail input and output and low input bias current, which makes this device suitable for a peak detector applications. Figure 3-7 shows a peak detector circuit with clear and sample switches. The peak-detection cycle uses a clock (CLK), as shown in Figure 3-7.

At the rising edge of CLK, Sample Switch closes to begin sampling. The peak voltage stored on C_1 is sampled to C_2 for a sample time defined by t_{SAMP} . At the end of the sample time (falling edge of Sample Signal), Clear Signal goes high and closes the Clear Switch. When the Clear Switch closes, C_1 discharges through R_1 for a time defined by t_{CLEAR} . At the end of the clear time (falling edge of Clear Signal), op amp A begins to store the peak value of V_{IN} on C_1 for a time defined by t_{DETECT} .

In order to define the t_{SAMP} and t_{CLEAR} , it is necessary to determine the capacitor charging and discharging period. The capacitor charging time is limited by the amplifier source current, while the discharging time (τ) is defined using R_1 ($\tau = R_1 \cdot C_1$). t_{DETECT} is the time that the input signal is sampled on C_1 , and is dependent on the input voltage change frequency.

The op amp output current limit, and the size of the storage capacitors (both C_1 and C_2), could create slewing limitations as the input voltage (V_{IN}) increases. Current through a capacitor is dependent on the size of the capacitor and the rate of voltage change. From this relationship, the rate of voltage change or the slew rate

can be determined. For example, with op amp short-circuit current of $I_{\text{SC}} = 25 \text{ mA}$ and load capacitor of $C_1 = 0.1 \mu\text{F}$, then:

EQUATION

$$\begin{aligned} I_{\text{SC}} &= C_1 \times \frac{dV_{C1}}{dt} \\ \frac{dV_{C1}}{dt} &= \frac{I_{\text{SC}}}{C_1} \\ &= \frac{25 \text{ mA}}{0.1 \mu\text{F}} \\ \frac{dV_{C1}}{dt} &= \frac{250 \text{ mV}}{\mu\text{s}} \end{aligned}$$

This voltage change rate is less than the MCP6001/2/4 slew rate of 600 mV/ μs . When the input voltage swings below the voltage across C_1 , D_1 becomes reverse-biased, which opens the feedback loop and rails the amplifier. When the input voltage increases, the amplifier recovers at its slew rate. Based on the rate of voltage change shown in the above equation, it takes an extended period of time to charge a 0.1 μF capacitor. The capacitors need to be selected so that the circuit is not limited by the amplifier slew rate. Therefore, the capacitors should be less than 40 μF and a stabilizing resistor (R_{ISO}) needs to be properly selected. Refer to Section 3.3, "Capacitive Load and Stability", for op amp stability.

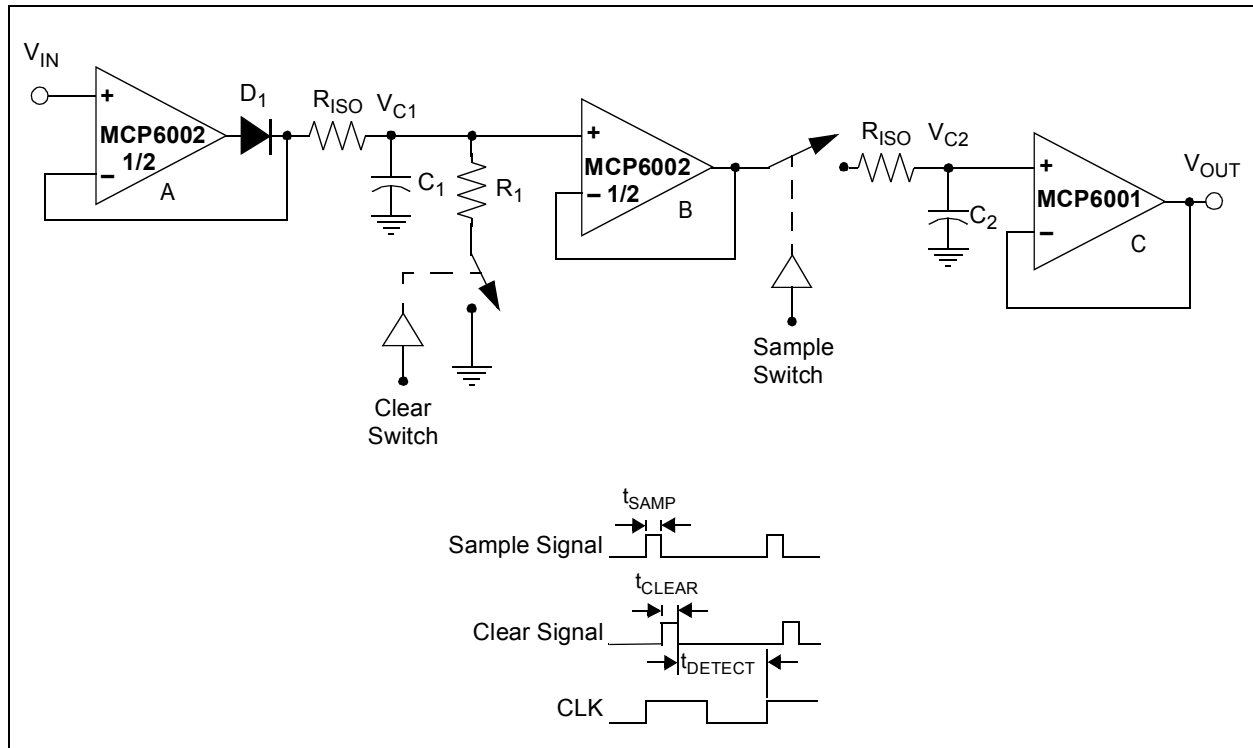


FIGURE 3-7: Peak Detector with Clear and Sample CMOS Analog Switches.